安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO. , LTD.

SS52F-SS510F

SMAF Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

■Features 特点

Low forward voltage drop 低正向压降
High current capability 高电流能力
Surface mount device 表面贴装器件
Case 封装:SMAF

SMAF

■Maximum Rating 最大额定值

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃)

Characteristic 特性参数	Symbol 符号	SS52F	SS53F	SS54F	SS55F	SS56F	SS58F	SS59F	SS510F	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	20	30	40	50	60	80	90	100	V
DC Reverse Voltage 直流反向电压	V_R	20	30	40	50	60	80	90	100	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	14	21	28	35	42	56	63	70	V
Forward Rectified Current 正向整流电流	I_F	5								A
Peak Surge Current 峰值浪涌电流	I_{FSM}	120								A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	10								℃/W
Junction Temperature 结温	T_J	150								℃
Storage Temperature 储藏温度	T_{stg}	-65to+150℃								℃

■Electrical Characteristics 电特性

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃)

Characteristic 特性参数	Symbol 符号	SS52F-SS54F	SS55F-SS56F	SS58F-SS510F	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F	0.55	0.70	0.85	V	I_F=5A
Reverse Current 反向电流	I_R(25℃) (100℃)	0.1 5		0.02 2	mA	V_R=V_{RRM}
Diode Capacitance 二极管电容	C_D	380			pF	V_R=4V,f=1MHz

■Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

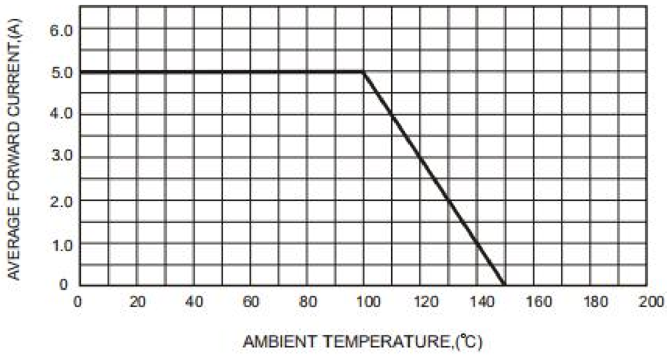


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

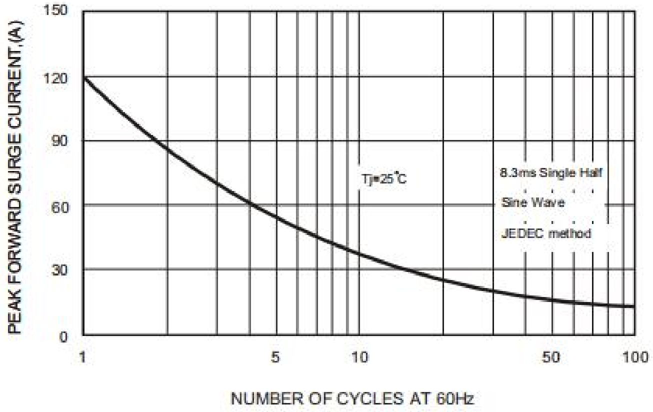


FIG.4-TYPICAL JUNCTION CAPACITANCE

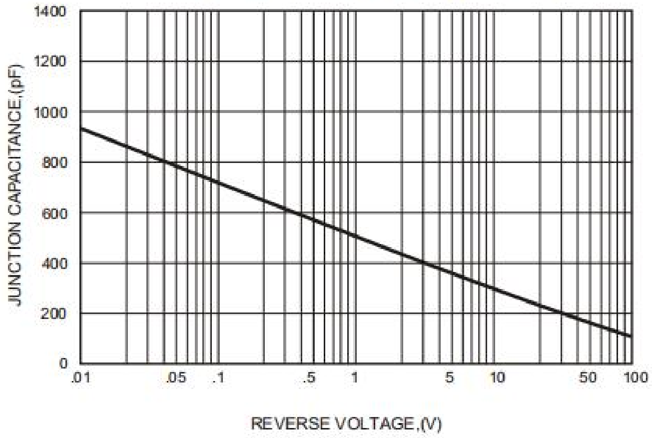


FIG.2-TYPICAL FORWARD CHARACTERISTICS

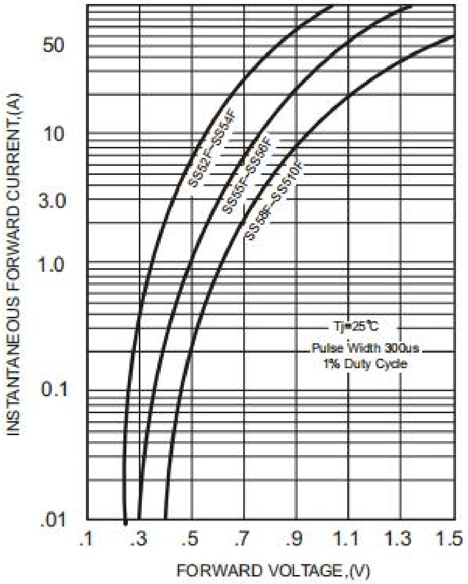
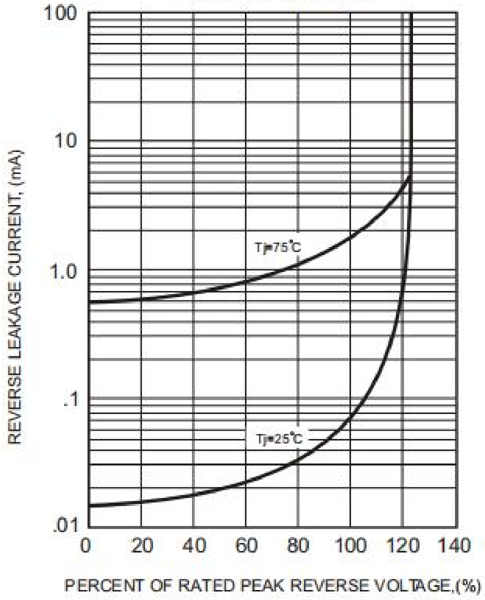
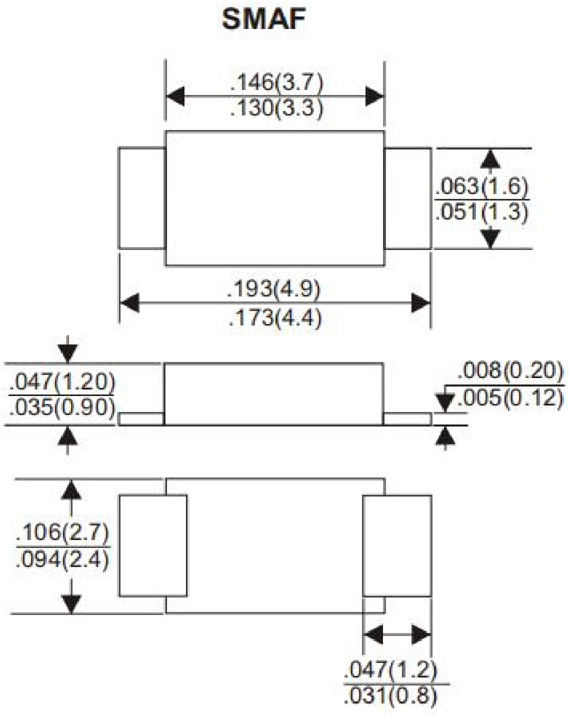


FIG.5 - TYPICAL REVERSE CHARACTERISTICS



■Dimension 外形封装尺寸



Dimensions in inches and (millimeters)